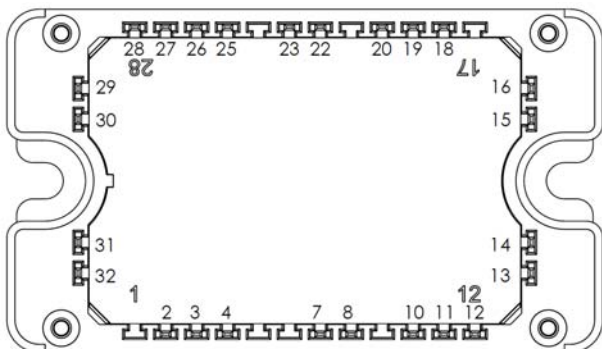
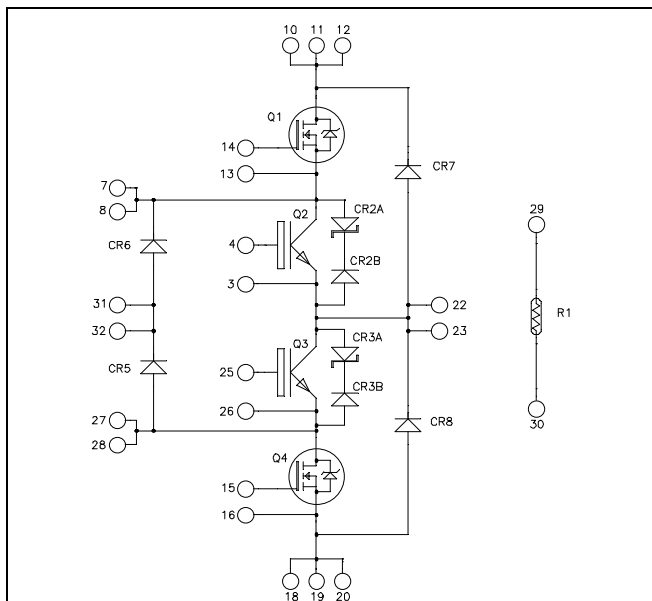


Three level inverter Power Module

Trench & Field Stop IGBT3 Q2, Q3:
 $V_{CES} = 600V$; $I_C = 30A$ @ $T_c = 80^\circ C$

Super junction MOSFET Q1, Q4:
 $V_{DSS} = 600V$; $I_D = 17A$ @ $T_c = 80^\circ C$



All multiple inputs and outputs must be shorted together
 Example: 10/11/12 ; 7/8 ...

Application

- Solar converter
- Uninterruptible Power Supplies

Features

- **Q2, Q3 Trench + Field Stop IGBT3**

- Low voltage drop
- Low tail current
- Switching frequency up to 20 kHz
- Low leakage current
- RBSOA and SCSOA rated

- **Q1, Q4 Super junction MOSFET**

- Ultra low R_{DSon}
- Low Miller capacitance
- Ultra low gate charge
- Avalanche energy rated
- Very rugged

- Kelvin emitter for easy drive
- Very low stray inductance
- High level of integration
- Internal thermistor for temperature monitoring

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile
- RoHS Compliant

All ratings @ $T_j = 25^\circ C$ unless otherwise specified

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

Q1 & Q4 Absolute maximum ratings (per Super junction MOSFET)

Symbol	Parameter	Max ratings	Unit
V_{DS}	Drain - Source Voltage	600	V
I_D	Continuous Drain Current	$T_c = 25^\circ\text{C}$	A
		$T_c = 80^\circ\text{C}$	
I_{DM}	Pulsed Drain current	75	
V_{GS}	Gate - Source Voltage	± 20	V
$R_{DS(on)}$	Drain - Source ON Resistance	99	m Ω
P_D	Power Dissipation	$T_c = 25^\circ\text{C}$	W
I_{AR}	Avalanche current (repetitive and non repetitive)	11	A
E_{AR}	Repetitive Avalanche Energy	1.2	mJ
E_{AS}	Single Pulse Avalanche Energy	800	

Q1 & Q4 Electrical Characteristics (per Super junction MOSFET)

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V$; $V_{DS} = 600V$			50	μA
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10V$, $I_D = 18A$			99	m Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 1.2\text{ mA}$	2.5	3	3.5	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 20\text{ V}$, $V_{DS} = 0V$			100	nA

Q1 & Q4 Dynamic Characteristics (per Super junction MOSFET)

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0V$; $V_{DS} = 100V$ $f = 1\text{MHz}$		2800		pF
C_{oss}	Output Capacitance			130		
Q_g	Total gate Charge	$V_{GS} = 10V$ $V_{Bus} = 400V$ $I_D = 18A$		14		nC
Q_{gs}	Gate – Source Charge			20		
Q_{gd}	Gate – Drain Charge			60		
$T_{d(on)}$	Turn-on Delay Time	$V_{GS} = 10V$ $V_{Bus} = 400V$ $I_D = 18A$ $R_G = 3.3\Omega$		10		ns
T_r	Rise Time			5		
$T_{d(off)}$	Turn-off Delay Time			60		
T_f	Fall Time			5		
R_{thJC}	Junction to Case Thermal Resistance				1.15	$^\circ\text{C/W}$

Q2 & Q3 Absolute maximum ratings (per IGBT)

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Voltage	600	V
I_C	Continuous Collector Current	$T_c = 25^\circ\text{C}$	A
		$T_c = 80^\circ\text{C}$	
I_{CM}	Pulsed Collector Current	$T_c = 25^\circ\text{C}$	60
V_{GE}	Gate – Emitter Voltage	± 20	V
P_D	Power Dissipation	$T_c = 25^\circ\text{C}$	90
$RBSOA$	Reverse Bias Safe Operating Area	$T_J = 150^\circ\text{C}$	60A @ 550V

Q2 & Q3 Electrical Characteristics (per IGBT)

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$			250	μA
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$V_{GE} = 15V$ $I_C = 30A$		1.5 1.7	1.9	V
		$T_j = 25^\circ C$ $T_j = 150^\circ C$				
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 400\mu A$	5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$			300	nA

Q2 & Q3 Dynamic Characteristics (per IGBT)

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$ $f = 1MHz$		1600		pF
C_{oes}	Output Capacitance			110		
C_{res}	Reverse Transfer Capacitance			50		
Q_G	Gate charge	$V_{GE} = \pm 15V, I_C = 30A$ $V_{CE} = 300V$		0.3		μC
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ($25^\circ C$) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 30A$ $R_G = 10\Omega$		110		ns
T_r	Rise Time			45		
$T_{d(off)}$	Turn-off Delay Time			200		
T_f	Fall Time			40		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ($150^\circ C$) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 30A$ $R_G = 10\Omega$		120		ns
T_r	Rise Time			50		
$T_{d(off)}$	Turn-off Delay Time			250		
T_f	Fall Time			60		
E_{on}	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 30A$	$T_j = 25^\circ C$ $T_j = 150^\circ C$	0.16 0.3		mJ
E_{off}	Turn-off Switching Energy	$R_G = 10\Omega$	$T_j = 25^\circ C$ $T_j = 150^\circ C$	0.7 1.05		mJ
I_{sc}	Short Circuit data	$V_{GE} \leq 15V; V_{Bus} = 360V$ $t_p \leq 6\mu s; T_j = 150^\circ C$		150		A
R_{thJC}	Junction to Case Thermal Resistance				1.6	$^\circ C/W$

CR2 & CR3 diode ratings and characteristics (per device)

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V_F	Diode + tranzorb Forward Voltage	$I_F = 10A$		10		V
R_{thJC}	Junction to Case Thermal Resistance				8	$^\circ C/W$

CR5 & CR6 diode ratings and characteristics (per diode)

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V _{RRM}	Peak Repetitive Reverse Voltage				600	V
I _{RM}	Reverse Leakage Current	V _R =600V			25	μA
I _F	DC Forward Current	T _C = 80°C		30		A
V _F	Diode Forward Voltage	I _F = 30A		1.8	2.2	V
		I _F = 60A		2.2		
		I _F = 30A T _j = 125°C		1.5		
t _{rr}	Reverse Recovery Time	I _F = 30A V _R = 400V di/dt = 200A/μs	T _j = 25°C	25		ns
			T _j = 125°C	160		
Q _{rr}	Reverse Recovery Charge		T _j = 25°C	35		nC
			T _j = 125°C	480		
E _{rr}	Reverse Recovery Energy	I _F = 30A V _R = 400V di/dt = 1000A/μs	T _j = 125°C	0.6		mJ
R _{thJC}	Junction to Case Thermal Resistance				1.2	°C/W

CR7 & CR8 diode ratings and characteristics (per diode)

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V _{RRM}	Peak Repetitive Reverse Voltage				1200	V
I _{RM}	Reverse Leakage Current	V _R =1200V			100	μA
I _F	DC Forward Current	T _C = 80°C		30		A
V _F	Diode Forward Voltage	I _F = 30A		2.6	3.1	V
		I _F = 60A		3.2		
		I _F = 30A T _j = 125°C		1.8		
t _{rr}	Reverse Recovery Time	I _F = 30A V _R = 800V di/dt = 200A/μs	T _j = 25°C	300		ns
			T _j = 125°C	380		
Q _{rr}	Reverse Recovery Charge		T _j = 25°C	360		nC
			T _j = 125°C	1700		
E _{rr}	Reverse Recovery Energy	I _F = 30A V _R = 800V di/dt = 1000A/μs	T _j = 125°C	1.6		mJ
R _{thJC}	Junction to Case Thermal Resistance				1.2	°C/W

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic	Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C		50		kΩ
ΔR ₂₅ /R ₂₅			5		%
B _{25/85}	T ₂₅ = 298.15 K		3952		K
ΔB/B	T _C =100°C		4		%

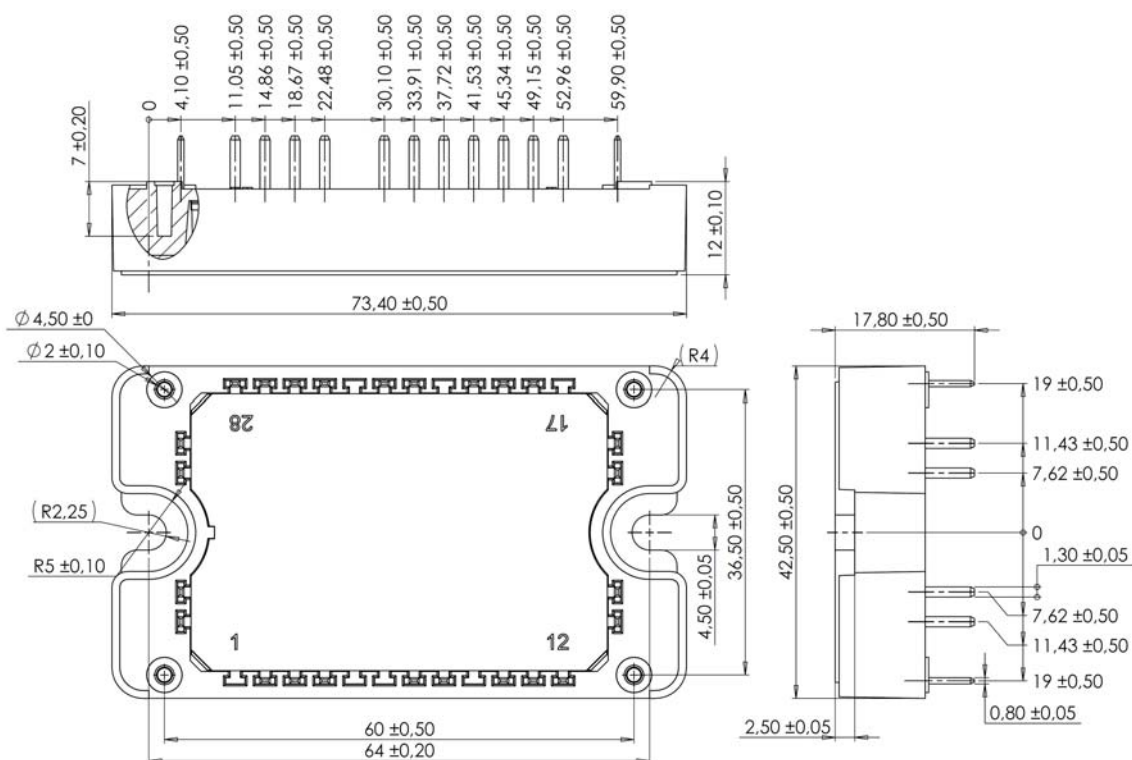
$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$

T: Thermistor temperature
 R_T: Thermistor value at T

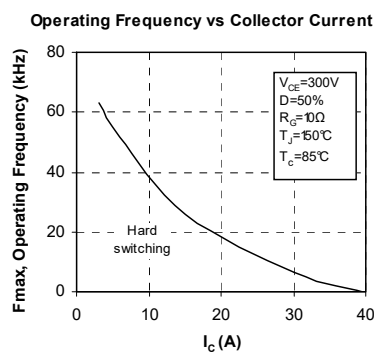
Thermal and package characteristics

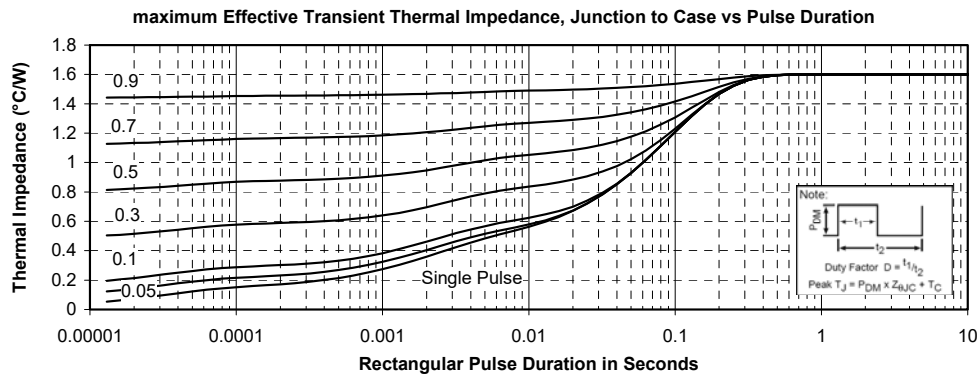
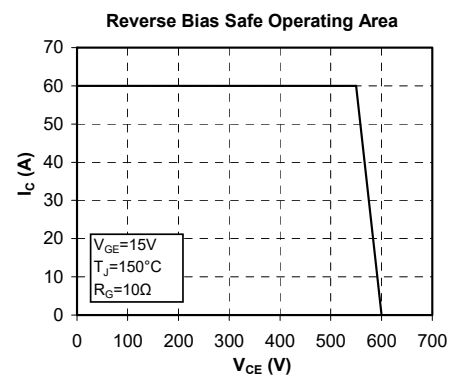
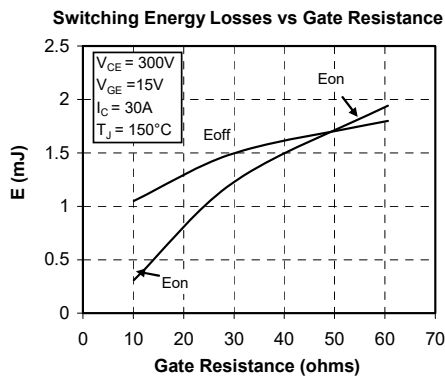
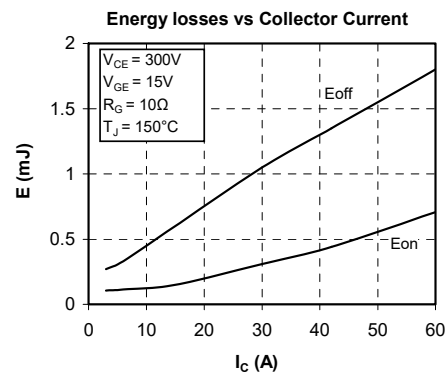
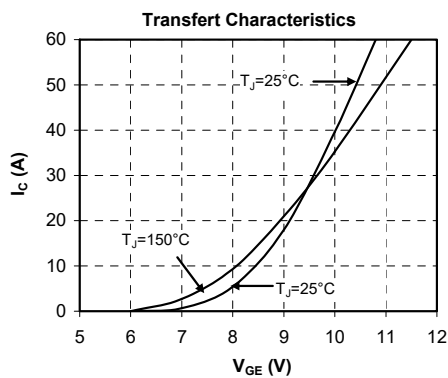
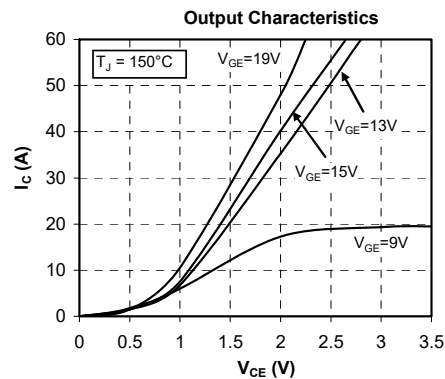
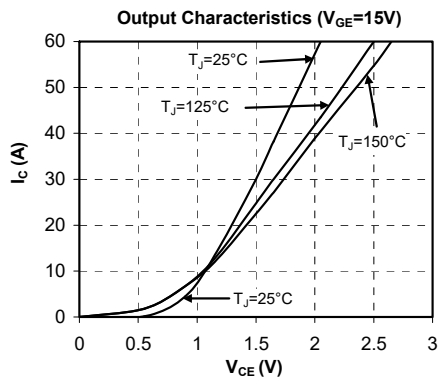
Symbol	Characteristic	Min	Max	Unit
V _{ISOL}	RMS Isolation Voltage, any terminal to case t=1 min, 50/60Hz	4000		V
T _J	Operating junction temperature range	-40	175*	°C
T _{JOP}	Recommended junction temperature under switching conditions	-40	T _{Jmax} -25	
T _{STG}	Storage Temperature Range	-40	125	
T _C	Operating Case Temperature	-40	125	
Torque	Mounting torque	To heatsink	M4	N.m
Wt	Package Weight		110	g

* T_{Jmax} = 150°C for Q1 & Q4

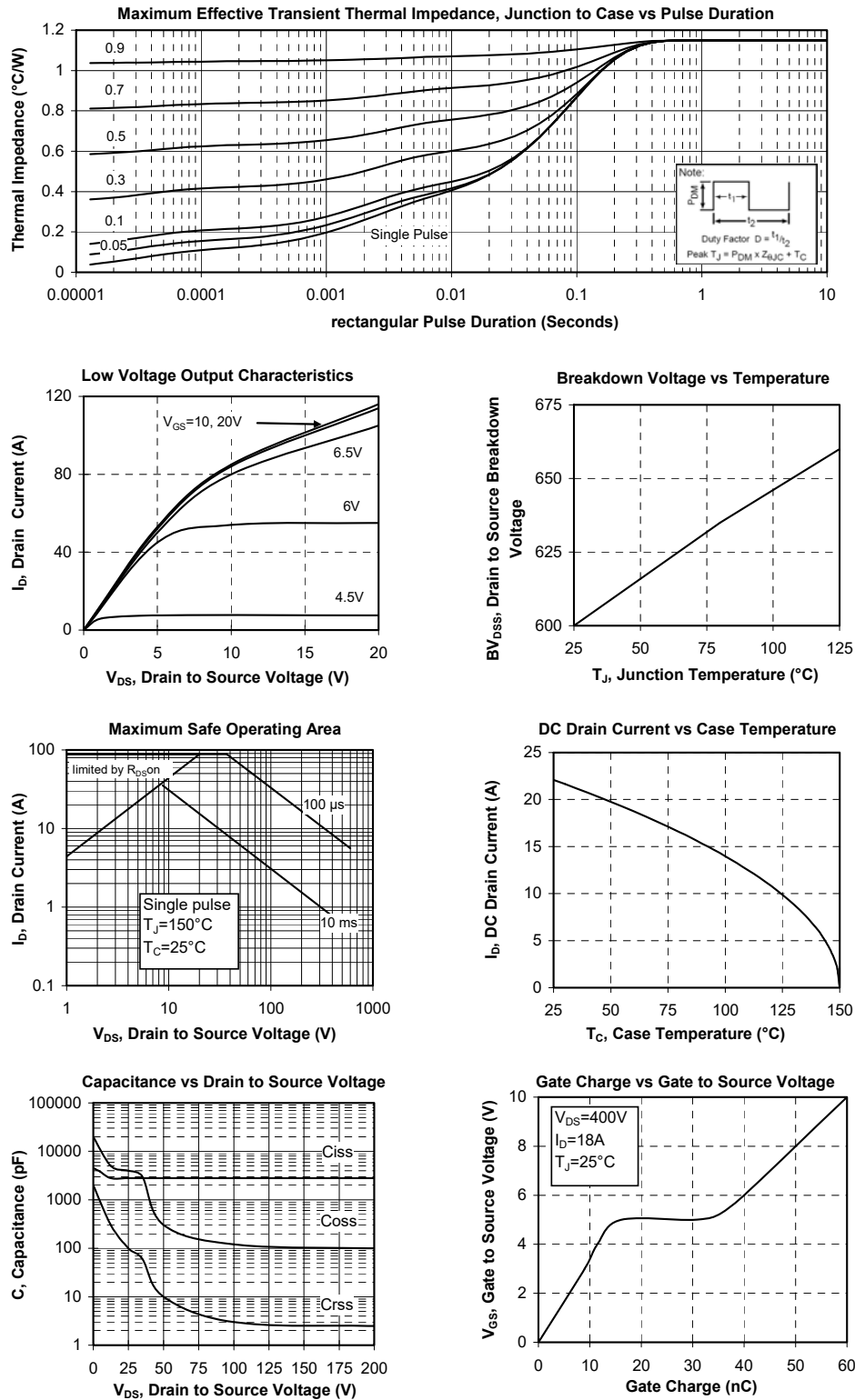
Package outline (dimensions in mm)


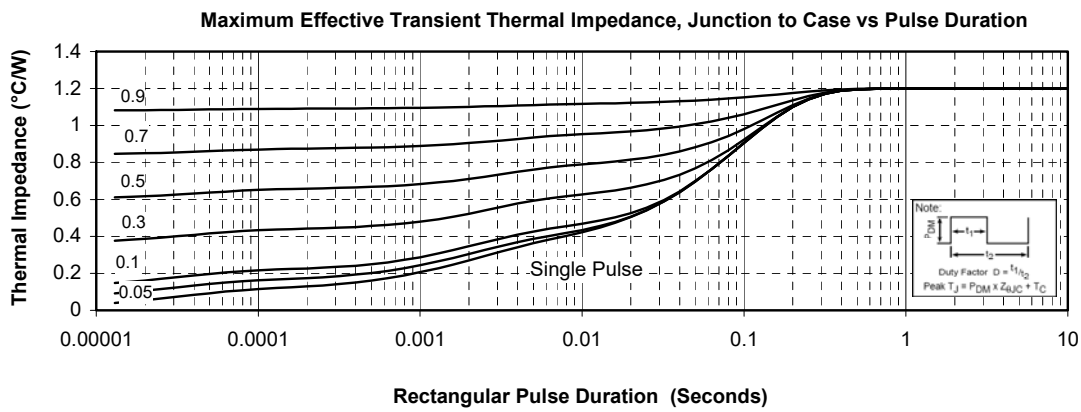
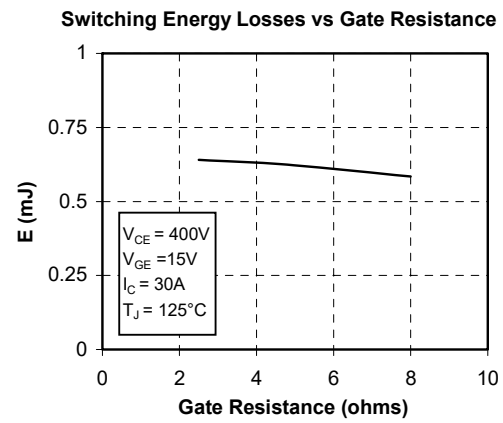
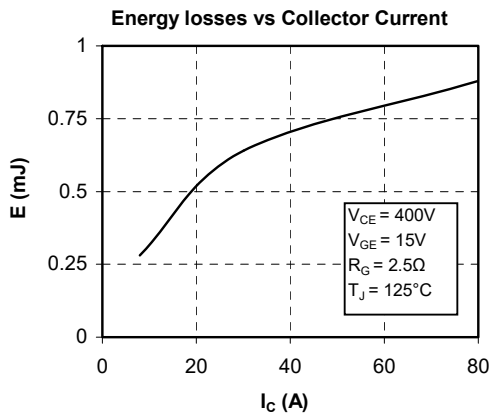
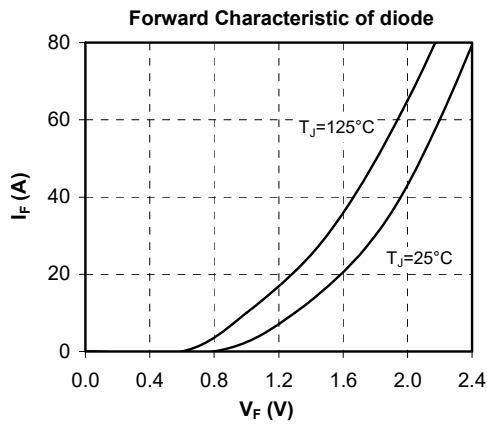
See application note 1906 - Mounting Instructions for SP3F Power Modules on www.microsemi.com

Q2 & Q3 Typical performance curve


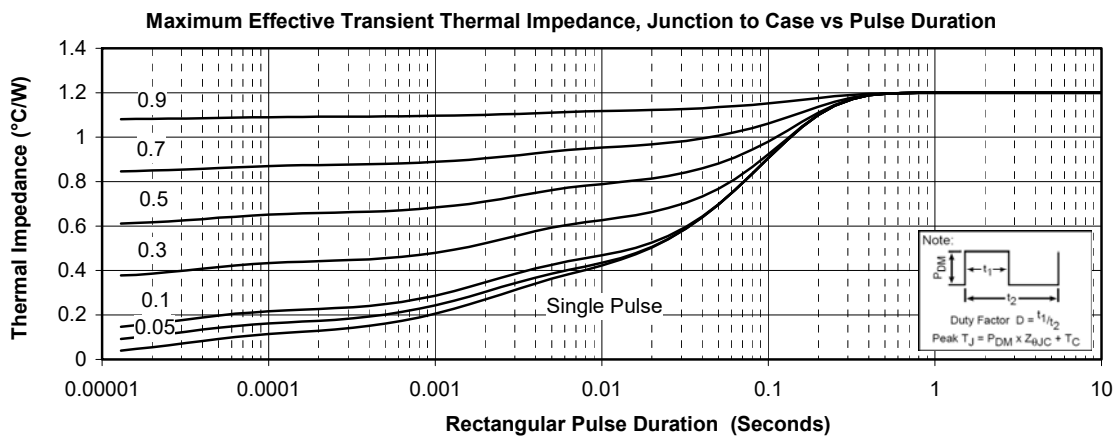
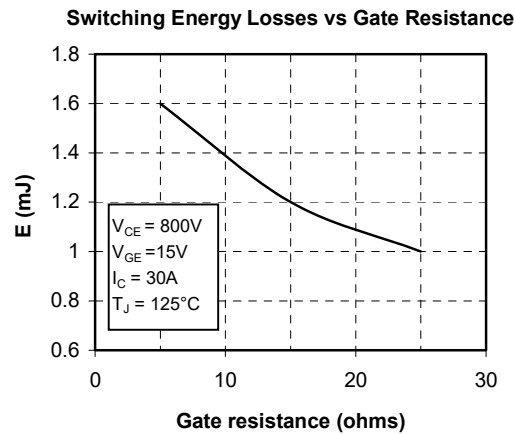
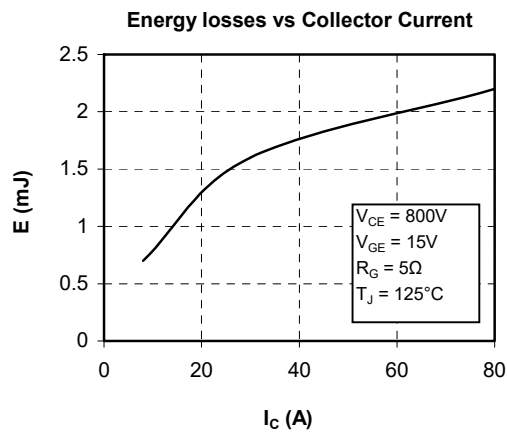
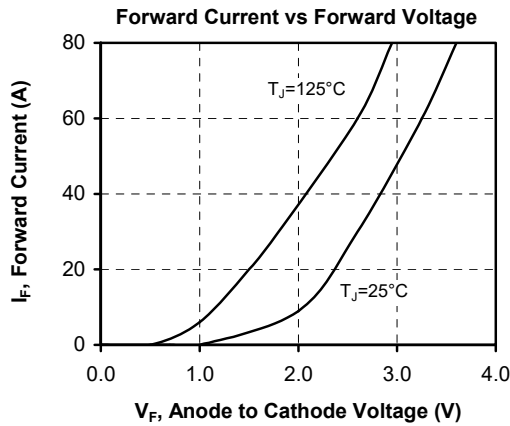


Q1 & Q4 Typical performance curve



CR5 & CR6 Typical performance curve


CR7 & CR8 Typical performance curve



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